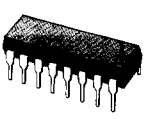
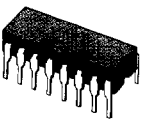
HEX D-TYPE FLIP FLOP WITH CLEAR

- HIGH SPEED
  f_{MAX} = 71 MHz (TYP.) AT V_{CC} = 5 V
- LOW POWER DISSIPATION
  I_{CC} = 4 µA (MAX.) AT T_A = 25 °C
- HIGH NOISE IMMUNITY
  $V_{NIH} = V_{NIL}$ = 28 % V_{CC} (MIN.)
- OUTPUT DRIVE CAPABILITY
  10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE
  $|I_{OH}| = I_{OL}$ = 4 mA (MIN.)
- BALANCED PROPAGATION DELAYS
  $t_{PLH} = t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE
  V_{CC} (OPR) = 2 V TO 6 V
- PIN AND FUNCTION COMPATIBLE WITH 54/74LS174



B1R
(Plastic Package)



F1R
(Ceramic Package)

M1R
(Micro Package)

C1R
(Chip Carrier)

ORDER CODES :

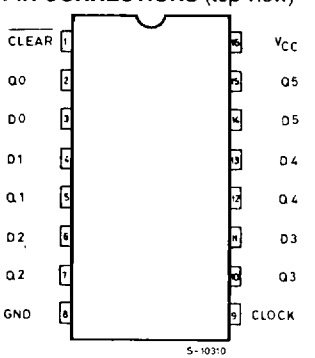
M54HC174F1R M74HC174M1R
M74HC174B1R M74HC174C1R

DESCRIPTION

The M54/74HC174 is a high speed CMOS HEX D-TYPE FLIP-FLOP WITH CLEAR fabricated in silicon gate C^2MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption.

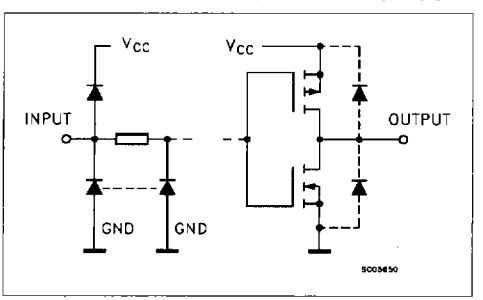
Information signals applied to D inputs are transfered to the Q output on the positive going edge of the clock pulse. When the $\overline{CLEAR}$ input is held low, the Q outputs are held low independently of the other inputs. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTIONS (top view)



NC = No Internal Connection

INPUT AND OUTPUT EQUIVALENT CIRCUIT



TRUTH TABLE

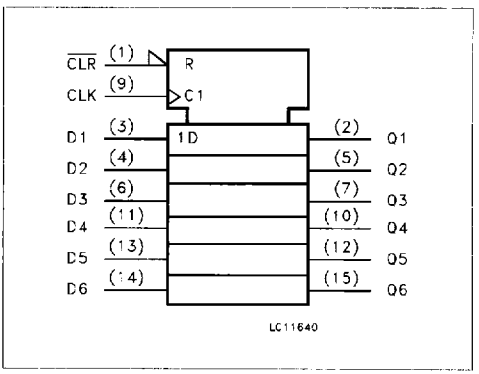
INPUTS			OUTPUTS	FUNCTION
CLEAR	D	CK	Q	
L	X	X	L	CLEAR
H	L	⌐	L	
H	H	⌐	H	
H	X	⌙	Q_n	NO CHANGE

X: Don't Care

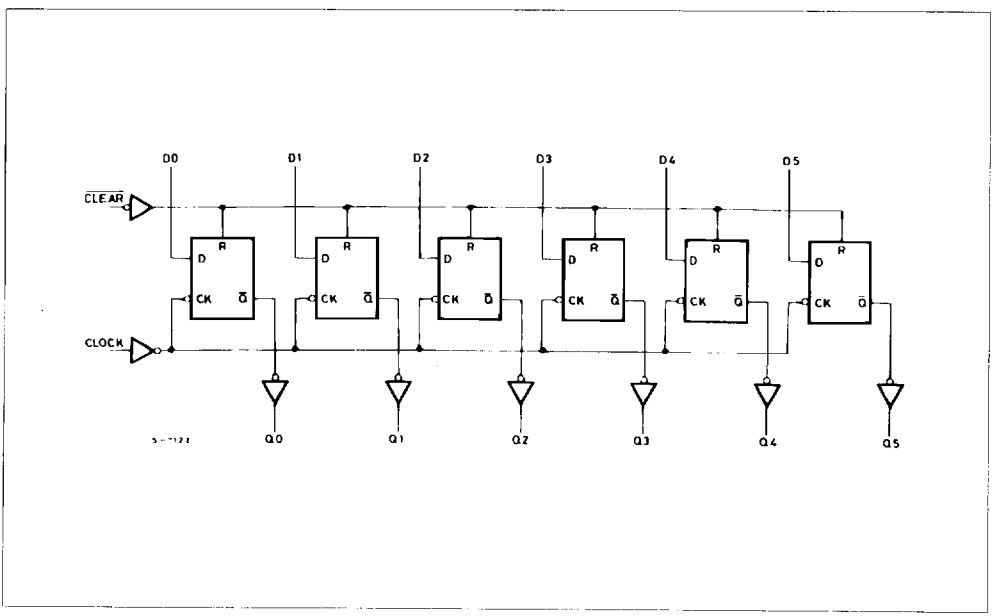
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1	$\overline{CLEAR}$	Asynchronous Master Reset (Active LOW)
2, 5, 7, 10, 12, 15	Q0 to Q5	Flip-flop Outputs
3, 4, 6, 11, 13, 14	D0 to D5	Data Inputs
9	CLOCK	Clock Input (LOW to HIGH, edge triggered)
8	GND	Ground (0V)
16	V_{CC}	Positive Supply Voltage

IEC LOGIC SYMBOL



LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7	V
V_I	DC Input Voltage	-0.5 to V_{CC} + 0.5	V
V_O	DC Output Voltage	-0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Source Sink Current Per Output Pin	± 25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 50	mA
P_D	Power Dissipation	500 (*)	mW
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.
(*) 500 mW: ≡ 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Value	Unit
V_{CC}	Supply Voltage		2 to 6	V
V_I	Input Voltage		0 to V_{CC}	V
V_O	Output Voltage		0 to V_{CC}	V
T_{op}	Operating Temperature: **M54HC** Series **M74HC** Series		-55 to +125 -40 to +85	°C °C
t_r, t_f	Input Rise and Fall Time	V_{CC} = 2 V	0 to 1000	ns
		V_{CC} = 4.5 V	0 to 500	
		V_{CC} = 6 V	0 to 400	

DC SPECIFICATIONS

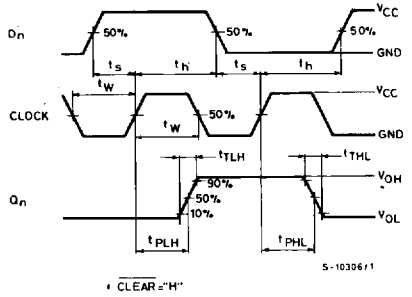
Symbol	Parameter	Test Conditions			Value							Unit
		V_{CC} (V)			T_A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	2.0			1.5			1.5		1.5		V
		4.5			3.15			3.15		3.15		
		6.0			4.2			4.2		4.2		
V_{IL}	Low Level Input Voltage	2.0					0.5		0.5		0.5	V
		4.5					1.35		1.35		1.35	
		6.0					1.8		1.8		1.8	
V_{OH}	High Level Output Voltage	2.0	V_I = V_{IH} or V_{IL}	I_O=-20 µA	1.9	2.0		1.9		1.9		V
		4.5			4.4	4.5		4.4		4.4		
		6.0			5.9	6.0		5.9		5.9		
		4.5		I_O=-4.0 mA	4.18	4.31		4.13		4.10		
		6.0		I_O=-5.2 mA	5.68	5.8		5.63		5.60		
V_{OL}	Low Level Output Voltage	2.0	V_I = V_{IH} or V_{IL}	I_O= 20 µA		0.0	0.1		0.1		0.1	V
		4.5				0.0	0.1		0.1		0.1	
		6.0				0.0	0.1		0.1		0.1	
		4.5		I_O= 4.0 mA		0.17	0.26		0.33		0.40	
		6.0		I_O= 5.2 mA		0.18	0.26		0.33		0.40	
I_I	Input Leakage Current	6.0	V_I = V_{CC} or GND				±0.1		±1		±1	µA
I_{CC}	Quiescent Supply Current	6.0	V_I = V_{CC} or GND				4		40		80	µA

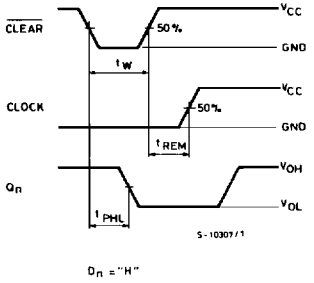
AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input $t_r = t_f$ = 6 ns)

Symbol	Parameter	Test Conditions		Value							Unit
		V_{CC} (V)		T_A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t_{TLH} t_{THL}	Output Transition Time	2.0			30	75		95		110	ns
		4.5			8	15		19		22	
		6.0			7	13		16		19	
t_{PLH} t_{PHL}	Propagation Delay Time (CK - Q)	2.0			68	135		170		205	ns
		4.5			17	27		34		41	
		6.0			14	23		29		35	
t_{PHL}	Propagation Delay Time ($\overline{CLR}$ - Q)	2.0			72	145		180		220	ns
		4.5			18	29		36		44	
		6.0			15	25		31		37	
f_{MAX}	Maximum Clock Frequency	2.0		7.2	14		5.8		4.8		MHz
		4.5		36	56		29		24		
		6.0		42	66		34		28		
$t_{W(H)}$ $t_{W(L)}$	Minimum Pulse Width ($\overline{CLOCK}$)	2.0			24	75		95		110	ns
		4.5			6	15		19		22	
		6.0			5	13		16		19	
$t_{W(L)}$	Minimum Pulse Width ($\overline{CLR}$)	2.0			24	75		95		110	ns
		4.5			6	15		19		22	
		6.0			5	13		16		19	
t_s	Minimum Set-up Time	2.0			28	75		95		110	ns
		4.5			7	15		19		22	
		6.0			6	13		16		19	
t_h	Minimum Hold Time	2.0				0		0		0	ns
		4.5				0		0		0	
		6.0				0		0		0	
t_{REM}	Minimum Removal Time	2.0			5	5		5		5	ns
		4.5			5	5		5		5	
		6.0			5	5		5		5	
C_{IN}	Input Capacitance				5	10		10		10	pF
C_{PD} (*)	Power Dissipation Capacitance				40						pF

(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operting current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/6$ (per FLIP/FLOP)
And the total CPD when N pcs of FLIP FLOP operate can be gained by the following equation: CPD (total)= 38 + 15 x n

SWITCHING CHARACTERISTICS TEST WAVEFORM





TEST CIRCUIT I_{CC} (Opr.)